



#### 60V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

60 V

Current

250mA

#### **Features**

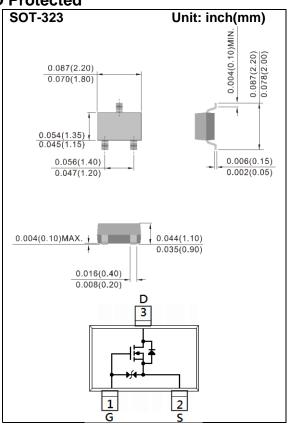
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@500mA<3Ω</li>
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@200mA<4Ω</li>
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- Very Low Leakage Current In Off Condition
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc
- ESD Protected 2KV HBM
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: SOT-323 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0002 ounces, 0.005 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER  |                      | SYMBOL          | LIMIT       | UNITS |  |
|--|----------------------|-----------------|-------------|-------|--|
| Drain-Source Voltage                             |                      | V <sub>DS</sub> | 60          | V     |  |
| Gate-Source Voltage                              |                      | $V_{GS}$        | <u>+</u> 20 |       |  |
| Continuous Drain Current                         |                      | I <sub>D</sub>  | 250         | mA    |  |
| Pulsed Drain Current                             |                      | I <sub>DM</sub> | 1000        |       |  |
| Power Dissipation                                | T <sub>a</sub> =25°C | P <sub>D</sub>  | 350         | mW    |  |
|  | Derate above 25°C    |                 | 2.8         | mW/°C |  |
| Operating Junction and Storage Temperature Range |                      | $T_J, T_{STG}$  | -55~150     | °C    |  |
| Typical Thermal Resistance                       |                      |                 |             |       |  |
| - Junction to Ambient (Note 3)                   |                      | $R_{\theta JA}$ | 357         | °C/W  |  |





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION   | MIN. | TYP. | MAX.        | UNITS    |  |
|----------------------------------|---------------------|--|------|------|-------------|----------|--|
| Static                           |                     |  |      |      |             |          |  |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V,I <sub>D</sub> =10uA   | 60   | -    | -           | -<br>2.5 |  |
| Gate Threshold Voltage           | $V_{GS(th)}$        | $V_{DS}=V_{GS}$ , $I_{D}=250uA$  | 1    | -    | 2.5         |          |  |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =10V,I <sub>D</sub> =500mA   | -    | -    | 3           | Ω        |  |
|                                  |                     | V <sub>GS</sub> =4.5V,I <sub>D</sub> =200mA  | -    | -    | 4           |          |  |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =60V,V <sub>GS</sub> =0V<br>V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V | -    | -    | 1           | uA       |  |
| Gate-Source Leakage Current      | I <sub>GSS</sub>    |  | -    | -    | <u>+</u> 10 |          |  |
| Forward Transconductance         | g <sub>fs</sub>     | V <sub>DS</sub> =15V, I <sub>D</sub> =250mA  | 100  | -    | -           | mS       |  |
| Dynamic (Note 5)                 |                     |  |      |      |             |          |  |
| Total Gate Charge                | $Q_g$               | V <sub>DS</sub> =15V, I <sub>D</sub> =250mA,<br>V <sub>GS</sub> =5V <sup>(Note 1,2)</sup>      | -    | 0.8  | -           | nC       |  |
| Gate-Source Charge               | $Q_gs$              |  | -    | 0.35 | -           |          |  |
| Gate-Drain Charge                | $Q_gd$              |  | -    | 0.2  | -           |          |  |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,<br>f=1MHZ   | -    | 24   | -           | pF       |  |
| Output Capacitance               | Coss                |  | -    | 13   | -           |          |  |
| Reverse Transfer Capacitance     | Crss                |  | -    | 8    | -           |          |  |
| Turn-On Delay Time               | td <sub>(on)</sub>  | $V_{DD}$ =30V, $I_{D}$ =200mA, $V_{GS}$ =10V, $R_{G}$ =10 $\Omega$ (Note 1,2)                  | -    | 3    | -           | ns       |  |
| Turn-On Rise Time                | tr                  |  | -    | 19   | -           |          |  |
| Turn-Off Delay Time              | td <sub>(off)</sub> |  | -    | 15   | -           |          |  |
| Turn-Off Fall Time               | tf                  |  | -    | 23   | -           |          |  |
| Drain-Source Diode               |                     |  |      |      |             |          |  |
| Maximum Continuous Drain-Source  |                     |  |      | 25   | 250         | mA       |  |
| Diode Forward Current            | I <sub>S</sub>      |  | -    |      | 250         |          |  |
| Diode Forward Voltage            | $V_{SD}$            | I <sub>S</sub> =200mA, V <sub>GS</sub> =0V   | -    | 0.82 | 1.3         | V        |  |

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

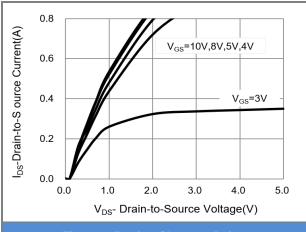
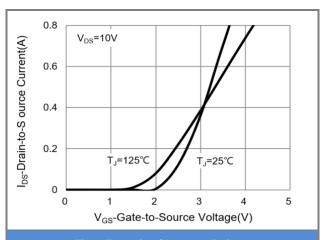


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

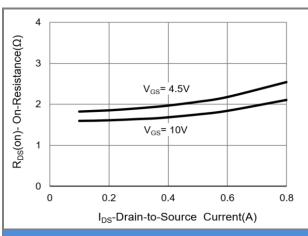


Fig.3 On-Resistance vs. Drain Current

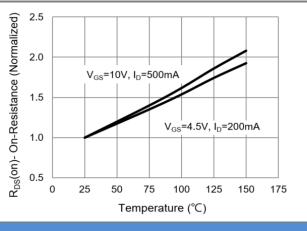


Fig.4 On-Resistance vs. Junction temperature

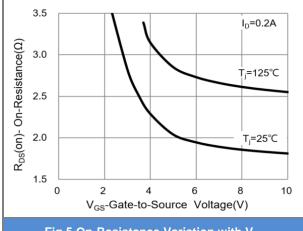


Fig.5 On-Resistance Variation with V<sub>GS</sub>

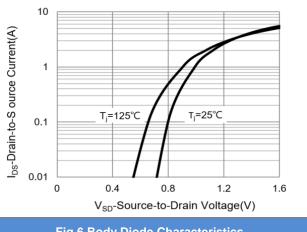
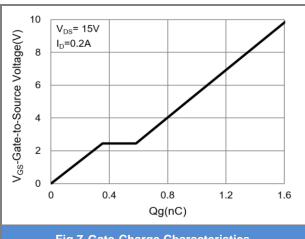


Fig.6 Body Diode Characteristics





#### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

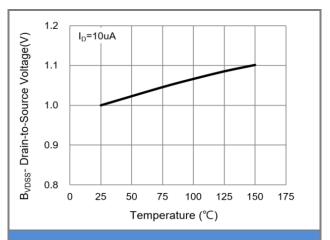


Fig.8 Breakdown Voltage Variation vs. Temperature

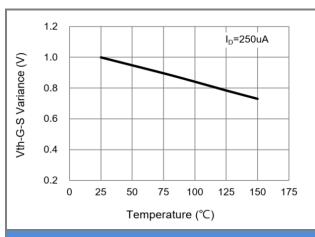


Fig.9 Threshold Voltage Variation with Temperature

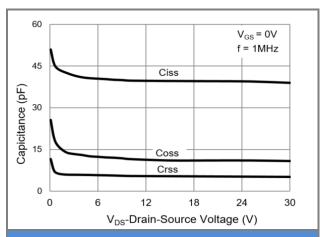


Fig.10 Capacitance vs. Drain-Source Voltage

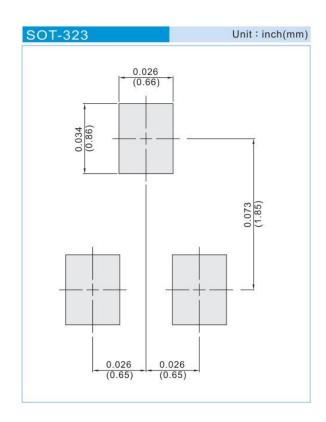




### **Part No Packing Code Version**

| Part No Packing Code | Package Type | Packing Type     | Marking | Version      |
|----------------------|--------------|------------------|---------|--------------|
| 2N7002KW-AU_R1_000A1 | SOT-323      | 3K pcs / 7" reel | K72     | Halogen free |

### **Mounting Pad Layout**







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